



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor: Matsudo

Group Art Unit: 2823

Application No.: 09/757,583

Examiner: Brairton, Scott A

Filing Date: 01/11/2001

For: METHOD FOR DEPOSITING TUNGSTEN SILICIDE FILM AND METHOD FOR  
PREPARING GATE ELECTRODE/WIRING

AMENDMENT AND RESPONSE TO OFFICE ACTION

Box Amendment  
Commissioner for Patents  
Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

A response to the Office Action mailed May 14, 2002 is being timely filed by the  
August 14, 2002 due date. Applicants request amendment of the application as follows.

AMENDMENT OF THE CLAIMS

Please add new claims 16-21 as shown by the attached clean version of the new  
claims. Applicants have enclosed the requisite fees for the additional claims.

REMARKS

Upon entry of the amendments, claims 1-21 will be pending in the application.

The Examiner has indicated that claims 1-7 are allowable because the prior art of  
record fails to disclose a method of depositing a tungsten silicide layer using a  
phosphorous containing gas as claimed by the instant application.

The Examiner has also indicated that claims 9-11, 13, and 14 would be allowable  
if rewritten in independent form including all the limitations of their base claim and any  
intervening claim.